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# SIZING THE UCC3919 CHARGE-PUMP CAPACITOR

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## ABSTRACT

The UCC3919 works in most hot-swap designs with the charge-pump capacitance recommended in the UCC3919 data sheet. However, this capacitance may be inadequate in high-current designs. This application report describes a method to size the charge-pump capacitance to ensure proper UCC3919 operation in any hot-swap design.

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## 1 Introduction

An internal charge pump boosts the supply voltage to the UCC3919 linear current amplifier (LCA). This allows the LCA to drive a high-side, low-cost N-channel FET instead of a more expensive P-channel FET. Because of its high source impedance (i.e., 100 k $\Omega$ ), the charge-pump output voltage droops when the LCA turns on the hot-swap FET. The amount of droop increases with the gate voltage slew rate and capacitance. If the droop is large enough to trip the charge-pump UVLO comparator, then the LCA shuts off, and it is not possible to turn on the FET. The UCC3919 data sheet recommends a 0.01- $\mu$ F to 0.1- $\mu$ F external charge-pump capacitor to provide adequate charge. This capacitance range is satisfactory for low-to-moderate current hot-swap designs. High-current hot-swap designs that use a larger FET require more capacitance. Instead of a *one size fits all* approach to selecting the charge-pump capacitance, an equation that customizes the charge-pump capacitance to the application is desirable. This application report presents a practical model of the UCC3919 and derives such an equation. This equation also applies to the UCC2919, an industrial-grade version of the UCC3919.

## 2 Turnon

Figure 1 is a simplified circuit model of the UCC3919 that shows only the LCA, charge pump, and charge-pump comparator. The turnon voltages are shown in Figure 2.

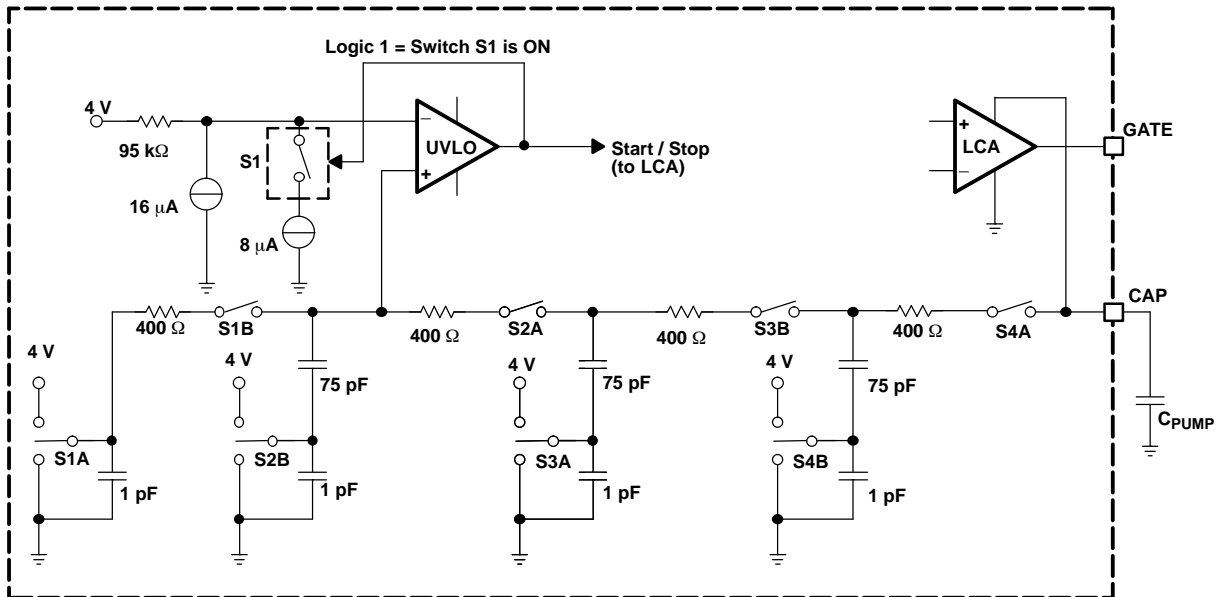


Figure 1. A Simplified UCC3919 Circuit Model

The UCC3919 charges capacitor  $C_{PUMP}$  when the  $\overline{SD}$  input de-asserts. The UVLO comparator enables the LCA when the capacitor voltage rises to  $V_{START}$ , the charge-pump UVLO minimum voltage to start. For the UCC3919 example in Figure 2,  $V_{START}$  is approximately 9 V. Figure 2 shows the UCC3919 turning on with different  $C_{PUMP}$  capacitors. Note that the hot-swap FET turnon delay is proportional to  $C_{PUMP}$ .

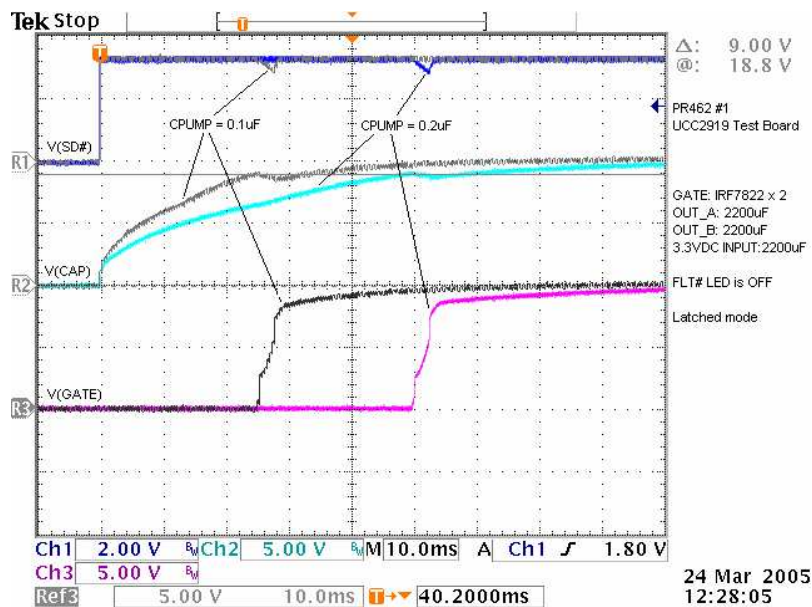


Figure 2. Typical UCC3919 Voltages at Turnon

### 3 SIZING $C_{PUMP}$ FOR A PARTICULAR APPLICATION

Figure 3 shows a gate-drive circuit model that can be used to calculate the charge-pump capacitance.

The  $R_O$  represents the equivalent LCA output resistance,  $V_{CAP}$  represents the charge-pump output voltage, and  $C_g$  models the FET gate capacitance. The charge-pump voltage  $V_{CAP}$  rises to  $V_{START}$  just before switch SW1 closes. The closing of switch SW1 models the LCA turning on. The voltage source  $V_{OUT}$  represents the load voltage when the hot-swap FET is on.

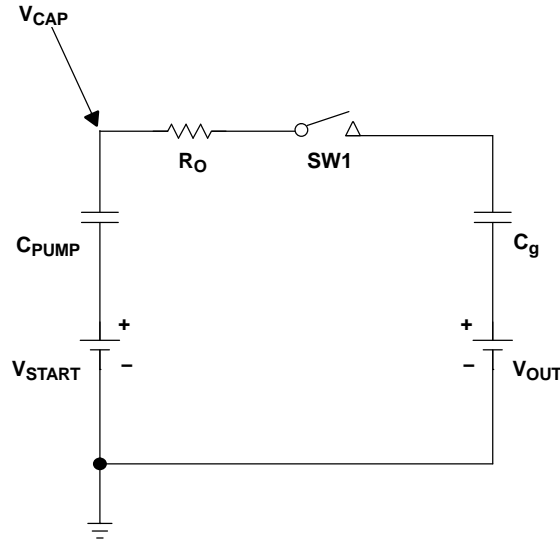


Figure 3. UCC3919 Gate-Drive Circuit Model.

When switch SW1 closes, charge from capacitor  $C_{PUMP}$  transfers to capacitor  $C_g$  causing the charge-pump voltage to drop by  $\Delta V_{CAP}$ . Equation 1 describes this relationship.

$$C_{PUMP} \times \frac{\mu Q_{PUMP}}{\mu V_{CAP}} \quad (1)$$

The charge lost by capacitor  $C_{PUMP}$  is gained by capacitor  $C_g$ .

$$\mu Q_{PUMP} = \mu Q_G \left( V_{GS} - V_{START} \times V_{OUT} \times V_{HYST} \right) \quad (2)$$

To ensure proper turnon, the charge-pump voltage droop must be less than the UVLO comparator hysteresis.

$$\mu V_{CAP} \times V_{HYST} \quad (3)$$

Combine equations (1), (2), and (3) to get Equation 4.

$$C_{PUMP} \geq \frac{\mu Q_G}{V_{HYST} \left( V_{GS} - V_{START} \times V_{OUT} \times V_{HYST} \right)} \quad (4)$$

For a worst-case calculation, use the maximum value for  $V_{START}$  and the minimum value for  $V_{HYST}$  in Equation 5.

UCC3919 production data over temperature and the  $V_{DD}$  supply voltage show that:

$$V_{START} (\text{max}) = 11 \text{ V}$$

$$V_{HYST} (\text{min}) = 0.7 \text{ V}$$

Therefore:

SUMMARY

$$C_{PUMP} \geq \frac{\mu Q_G}{0.7 V} \left| V_{GS} \right) 10.3 V \times V_{OUT} \tag{5}$$

As an example, consider a 3.3-V output hot-swap design that drives three IRF7822 FETs. The curve in Figure 4 shows 58.75 nC of gate charge for a gate-to-source voltage of 7 V. Thus, the required charge-pump capacitance is

$$C_{PUMP} \geq \frac{58.75 \text{ nC} \times 3}{0.7 V} = 0.252 \mu\text{F} \tag{6}$$

A standard 0.33-μF ± 10% X7R dielectric capacitor works for this design. Note that 10% is the capacitor's initial tolerance. This tolerance is measured at room temperature and zero-bias voltage. The actual tolerance is higher when the capacitor's operating temperature and operating voltage are considered.

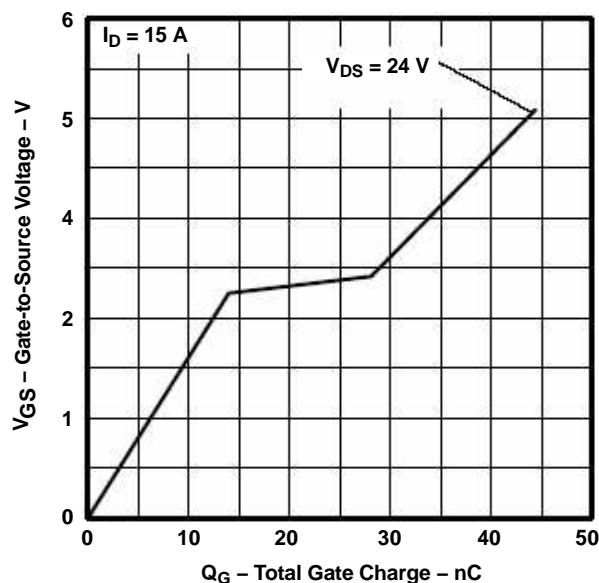


Figure 4. IRF7822 Gate Charge vs Gate-to-Source Voltage <sup>(1)</sup>

<sup>(1)</sup> Reprinted with permission from International Rectifier; Fig 2, page 3, International Rectifier IRF7822 datasheet.

**4 SUMMARY**

The UCC3919 works in a low-to-moderate current, hot-swap design with a 0.01-μF to 0.1-μF capacitance at the CAP pin as recommended in the data sheet (SLUS374). A high-current, hot-swap design that uses a larger FET requires more capacitance. This capacitance can be determined using the simple approach presented in this application report. The larger capacitance increases the hot-swap FET turnon delay but has no other effect on the UCC3919.

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